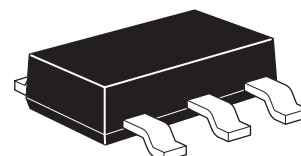


ZXMN10A25G

100V SOT223 N-channel enhancement mode MOSFET

Summary

$V_{(BR)DSS}$	$R_{DS(on)} (\Omega)$	$I_D (A)$
100	0.125 @ $V_{GS} = 10V$	4
	0.150 @ $V_{GS} = 6V$	3.7

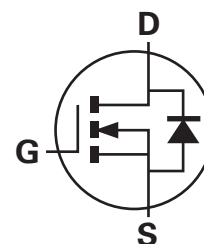


Description

This new generation trench MOSFET from Zetex features a unique structure which combines the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Features

- Low on-resistance
- Fast switching speed
- Low gate drive
- SOT223 package

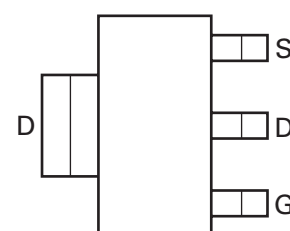


Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A25GTA	7	12	1,000



Pinout - top view

Device marking

ZXMN
10A25

ZXMN10A25G

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DSS}	100	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current @ $V_{GS} = 10V$; $T_{amb}=25^{\circ}C^{(b)}$ @ $V_{GS} = 10V$; $T_{amb}=70^{\circ}C^{(b)}$ @ $V_{GS} = 10V$; $T_{amb}=25^{\circ}C^{(a)}$	I_D	4 3.2 2.9	A
Pulsed drain current ^(c)	I_{DM}	17	A
Continuous source current (body diode) ^(b)	I_S	5.4	A
Pulsed source current (body diode) ^(c)	I_{SM}	17	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P_D	2	W
Linear derating factor		16	mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P_D	3.9	W
Linear derating factor		31	mW/ $^{\circ}C$
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Junction to ambient ^(b)	$R_{\theta JA}$	32	$^{\circ}C/W$

NOTES:

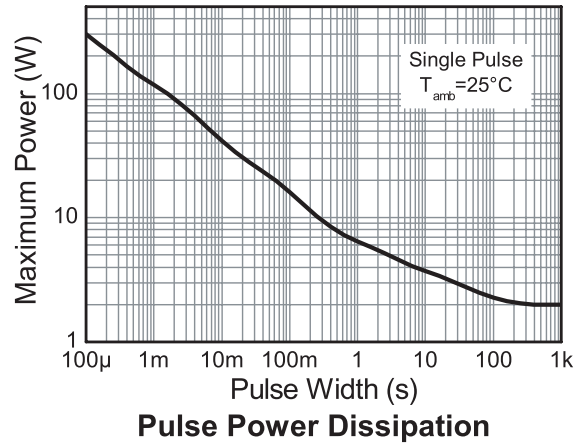
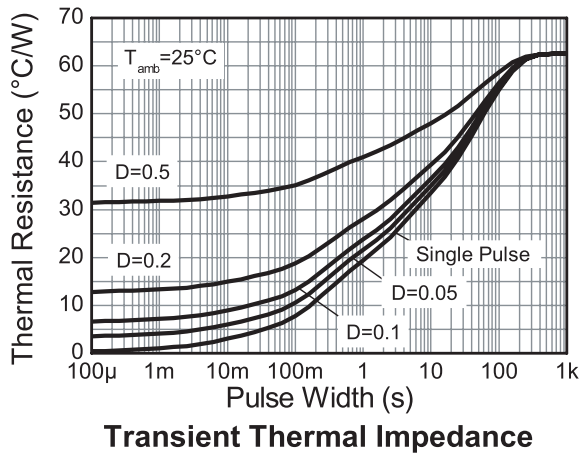
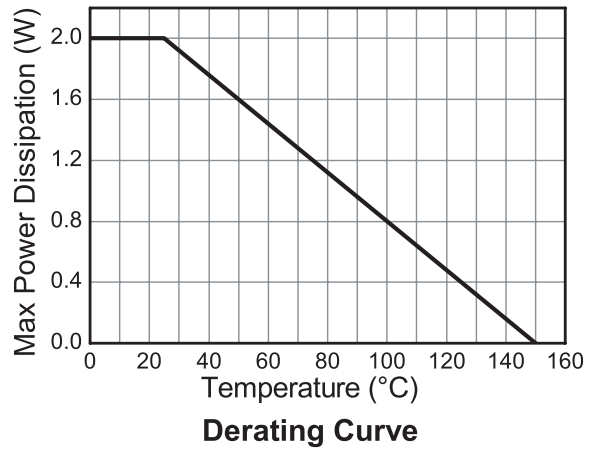
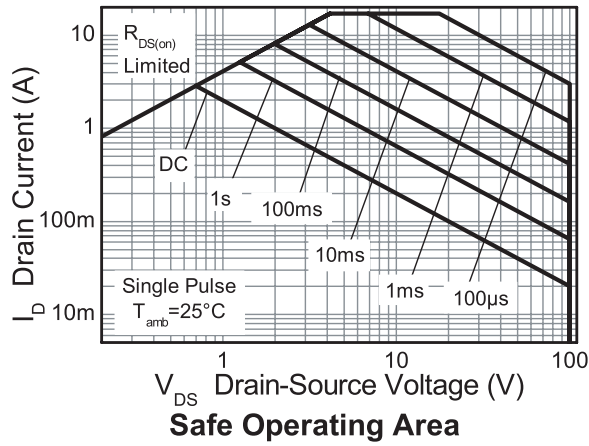
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.

(c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width $\leq 300\mu s$ - pulse width limited by maximum junction temperature.

ZXMN10A25G

Thermal characteristics



ZXMN10A25G

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	100			V	I _D = 250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			0.5	μA	V _{DS} = 100V, V _{GS} =0V
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-source threshold voltage	V _{GS(th)}	2.0		4.0	V	I _D = 250μA, V _{DS} =V _{GS}
Static drain-source on-state resistance ^(*)	R _{DS(on)}			0.125	Ω	V _{GS} = 10V, I _D = 2.9A
				0.150	Ω	V _{GS} = 6V, I _D = 2.6A
Forward transconductance ^{(*)(‡)}	g _{fs}		7.3		S	V _{DS} = 15V, I _D = 2.9A
Dynamic ^(‡)						
Input capacitance	C _{iss}		859		pF	V _{DS} = 50V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}		57		pF	
Reverse transfer capacitance	C _{rss}		33		pF	
Switching ^(†) (‡)						
Turn-on-delay time	t _{d(on)}		4.9		ns	V _{DD} = 50V, I _D = 1A R _G ≅6.0Ω, V _{GS} = 10V
Rise time	t _r		3.7		ns	
Turn-off delay time	t _{d(off)}		18		ns	
Fall time	t _f		9.4		ns	
Gate charge	Q _g		9.6		nC	V _{DS} = 50V, V _{GS} = 5V I _D = 2.9A
Total gate charge	Q _g		17		nC	V _{DS} = 50V, V _{GS} = 10V I _D = 2.9A
Gate-source charge	Q _{gs}		3.8		nC	
Gate drain charge	Q _{gd}		5.4		nC	
Source-drain diode						
Diode forward voltage ^(*)	V _{SD}		0.85	0.95	V	T _j =25°C, I _S = 4A, V _{GS} =0V
Reverse recovery time ^(‡)	t _{rr}		40.5		ns	T _j =25°C, I _S = 2.9A, di/dt=100A/μs
Reverse recovery charge ^(‡)	Q _{rr}		62		nC	

NOTES:

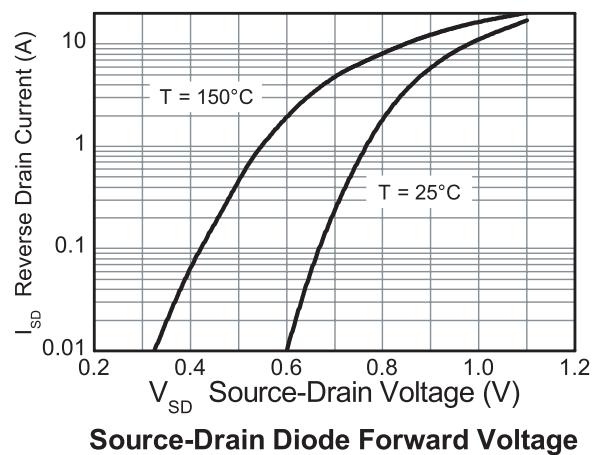
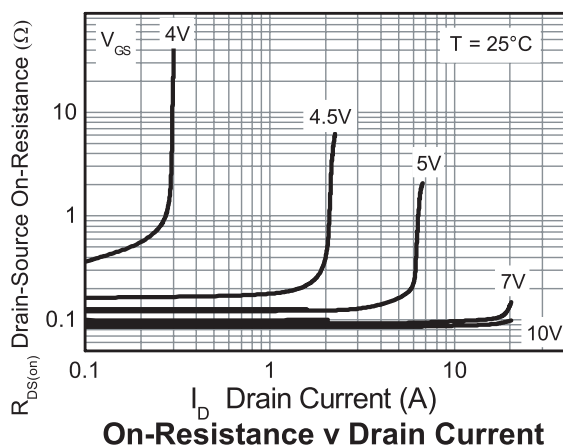
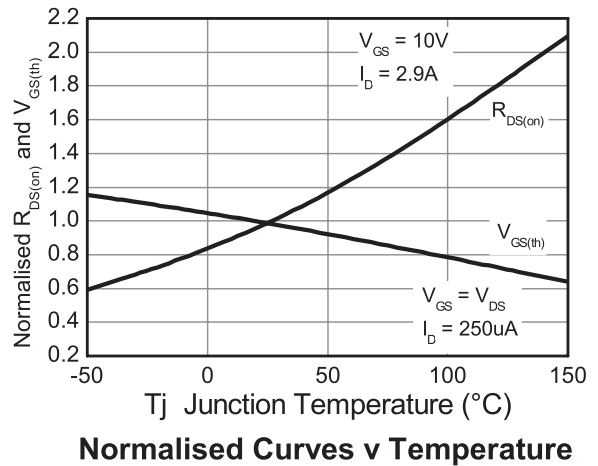
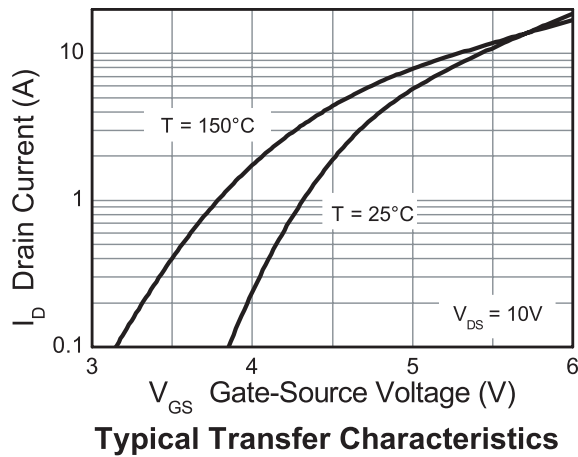
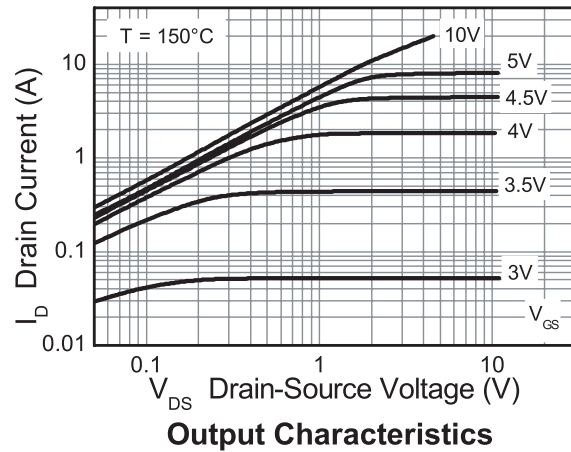
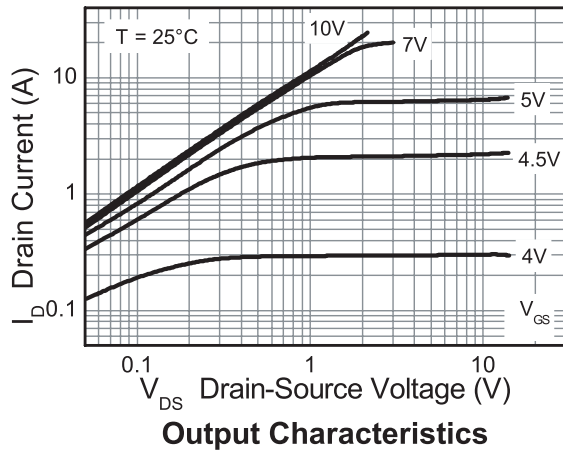
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

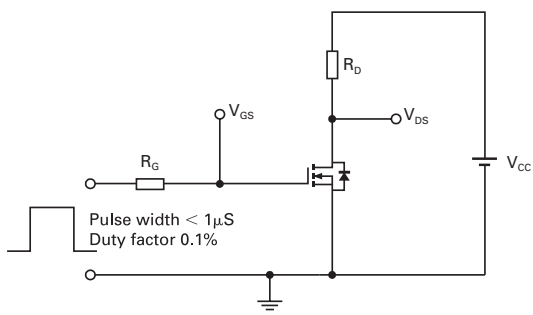
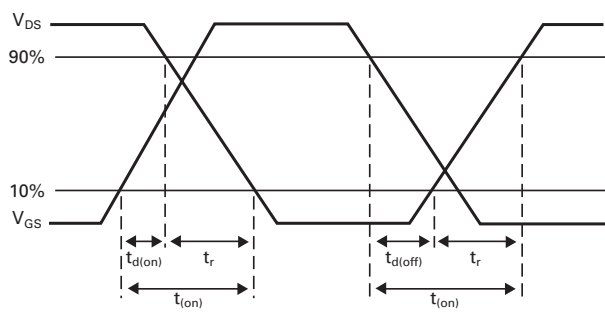
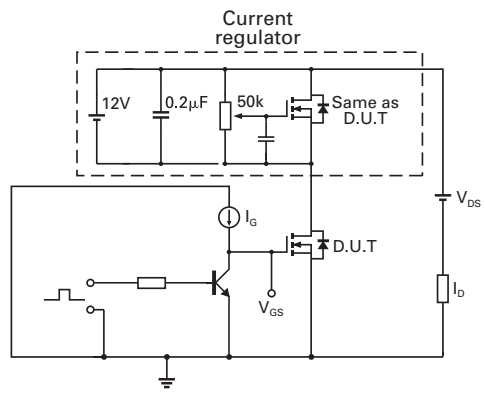
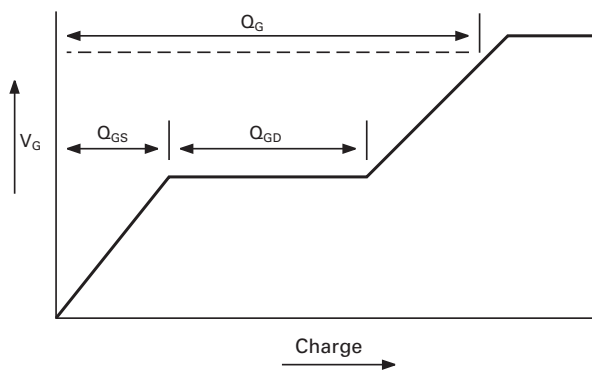
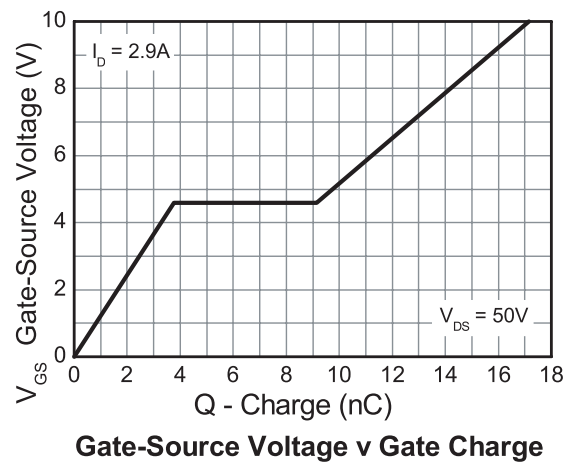
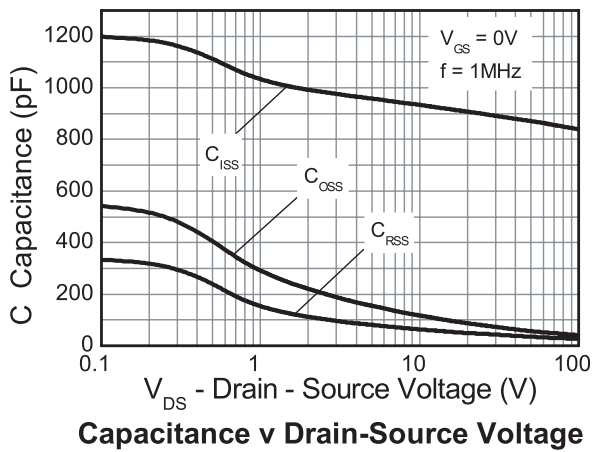
ZXMN10A25G

Typical Characteristics



ZXMN10A25G

Typical Characteristics

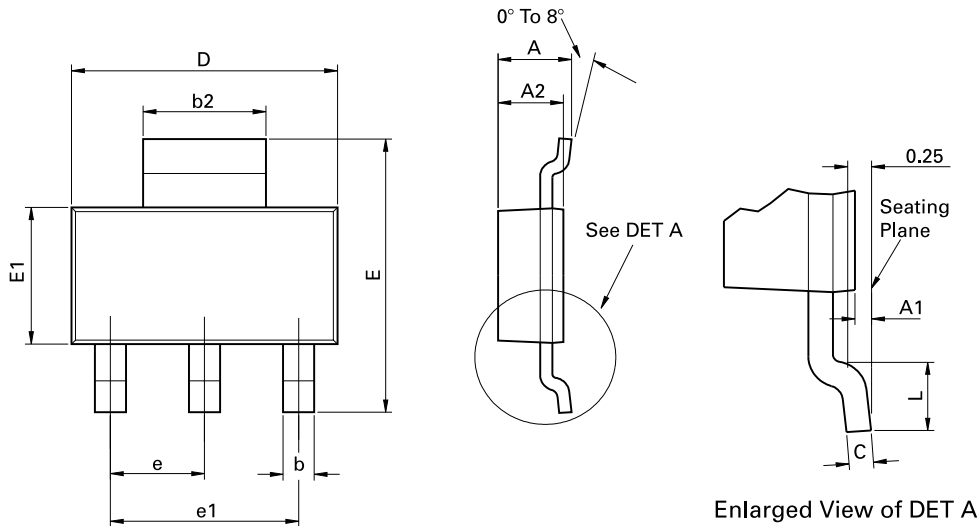


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ZXMN10A25G

Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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